

QUADRUPLE 2-INPUT NAND GATES

Description

The 74LVC00A provides four independent 2-input NAND gates. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down.

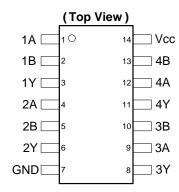
The gates perform the positive Boolean function:

$$Y = \overline{A \bullet B}$$
 or $Y = \overline{A} + \overline{B}$

Features

- Supply Voltage Range from 1.65V to 5.5V
- Sinks 24mA at V_{CC} = 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs or outputs accept up to 5.5V
- Inputs can be driven by 3.3V or 5.5V allowing for voltage translation applications.
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115-A)
 - 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 250mA per JESD 78, Class II
- Range of Package Options SO-14 and TSSOP-14
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



SO-14 / TSSOP-14

Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
 - PCs, networking, notebooks, ultrabooks, netbooks
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box

Notes:

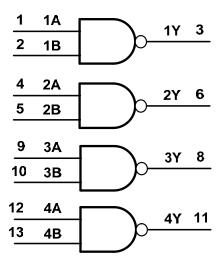
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

Pin Number	Pin Name	Function
1	1A	Data Input
2	1B	Data Input
3	1Y	Data Output
4	2A	Data Input
5	2B	Data Input
6	2Y	Data Output
7	GND	Ground
8	3Y	Data Output
9	3A	Data Input
10	3B	Data Input
11	4Y	Data Output
12	4A	Data Input
13	4B	Data Input
14	Vcc	Supply Voltage

Logic Diagram



Fuction Table

Inp	Output	
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L



Absolute Maximum Ratings (Note 4) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
Vı	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
l _{IK}	Input Clamp Current V _I < 0	-50	mA
lok	Output Clamp Current V _O < 0	-50	mA
Io	Continuous output current	±50	mA
I _{CC} ,, I _{GND}	Continuous current through Vcc or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C
P _{TOT}	Total Power Dissipation	500	mW

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	Supply Voltage		1.65	5.5	V
VI	Input Voltage		0	5.5	V
	Outrot Vallage	Active Mode	0	V _{CC}	V
Vo	Output Voltage	V _{CC} = 0V; Power Down Mode	0	5.5	V
A (/ A) /	Langet to a confession of all and a	V _{CC} = 1.65V to 2.7V		20	0.4
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 2.7V to 3.6V		10	ns/V
T _A	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at $V_{\mbox{CC}}$ or Ground.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

0	D	Tast Osmalitisms		$T_A = -40$ °C to		T _A = -40°C	to +125°C	1111	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Min	Max	Unit	
			1.65V to 1.95V	0.65 X V _{CC}		0.65 X V _{CC}			
V_{IH}	High-level Input		2.3V to 2.7V	1.7		1.6		V	
	Voltage		2.7 V to 3.6V	2.0		2.0			
			1.65V to 1.95V		0.35 X V _{CC}		0.35 X V _{CC}		
V_{IL}	Low-level input		2.3V to 2.7V		0.7		0.7	V	
	voltage		2.7V to 3.6V		0.8		0.8		
		$I_{OH} = -100 \mu A$	1.65V to 3.6V	V _{CC} - 0.2		V _{CC} - 0.3			
		I _{OH} = -4mA	1.65V	1.2					
\/	High Level	$I_{OH} = -8mA$	2.3V	1.9				.,	
V _{OH}	Output Voltage	Output Voltage	1. 12m A	2.7V	2.2		2.05		V
		I _{OH} = -12mA	3.0V 2.3	2.1					
		I _{OH} = -24mA	3.0V	2.2		2.0			
		I _{OH} = 100μA	1.65V to 3.6V		0.2		0.3	·	
		I _{OH} = 4mA	1.65V		0.45		0.6		
V	High-level	$I_{OH} = 8mA$	2.3V		0.70		0.85	V	
V_{OL}	Output Voltage	1. 10m A	2.7V		0.40		0.6	V	
		I _{OH} = 12mA	3.0V		0.55		0.6		
		I _{OH} =-24mA	3.0V		0.55		0.6		
I _I	Input Current	$V_I = GND \text{ to } 5.5V$	3.6V		±5		±20	μΑ	
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0		10		20	μΑ	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}$ $I_O=0$	3.6V		10		40	μΑ	
ΔI _{CC}	Additional Supply Current	One input at V _{CC} – 0.6V Other at Vcc or Gnd.	2.7V to 3.6V		500		5000	μΑ	

Switching Characteristics

Symbol Parameter		Test	V	T _A = 25°C		-40°C to 85°C		-40°C to 125°C		Unit	
		Conditions	V _{cc}	Min	Тур	Max	Min	Max	Min	Max	Ollit
Propagation		1.65V to1.95V	1.0	6.0	12.0	1.0	12.5	1.0	14.0		
	- 4	2.3V to 2.7V	1.0	4.6	5.9	1.0	6.4	1.0	7.9		
t _{PD}	Delay A _N or B _N to Y _N	Figure 1	2.7V	1.0	4.3	4.9	1.0	5.1	1.0	6.5	ns
IO TN		3V to 3.6V	1.0	3.5	4.1	1.0	4.3	1.0	5.5		
Output Skew			2\/ to 2 6\/					1.0		1.5	20
t _{SK(0)}	Time		3V to 3.6V					1.0		1.5	ns



Operating Characteristics (@T_A = +25°C, unless otherwise specified.)

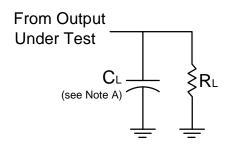
	Parameter	Test Conditions	V _{CC} = 1.8V Typ	V _{CC} = 2.5V Typ	V _{CC} = 3.3V Typ	Unit
C_{pd}	Power dissipation capacitance per gate	f = 10 MHz	17	17	18	pF
Cı	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	4	4	4	pF

Package Characteristics

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур	Max	Unit
0	Thermal Resistance	SO-14	(Nata 0)		TBD		°C/W
θ_{JA}	Junction-to-Ambient	TSSOP-14	(Note 6)		159		
0	Thermal Resistance	SO-14	(Note 6)		TBD		°C/W
θ _{JC}	Junction-to-Case	TSSOP-14	TSSOP-14 (Note 6)		25		G/ VV

Note: 6. Test condition for SO-14 and TSSOP-14: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Parameter Measuement Information

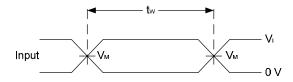


V	Inj	outs	V		В	
V _{CC}	V _I	t _r /t _f	V _M	CL	KL	
1.8V±0.15V	Vcc	≤2ns	V _{CC} /2	30pF	1ΚΩ	
2.5V±0.2V	Vcc	≤2ns	V _{CC} /2	30pF	500Ω	
2.7V	2.7V	≤2.5ns	1.5V	50pF	500Ω	
3.3V±0.3V	2.7V	≤2.5ns	1.5V	50pF	500Ω	

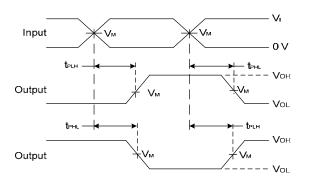
June 2012



Parameter Measuement Information (cont.)



Voltage Waveform Pulse Duration



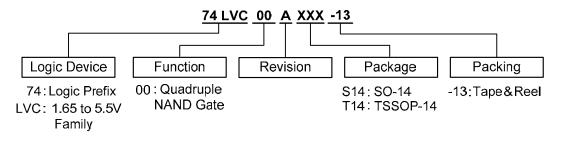
Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A . Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz
 C. Inputs are measured separately one transition per measurement
- D. tpLH and tpHL are the same as tpD

Figure 1. Load Circuit and Voltage Waveforms

Ordering Information





Part	Package	Packaging	13" Tape and Reel	
Number	Code	(Note 7)	Quantity	Part Number Suffix
74LVC00AS14-13	S14	SO-14	2500/Tape & Reel	-13
74LVC00AT14-13	T14	TSSOP-14	2500/Tape & Reel	-13

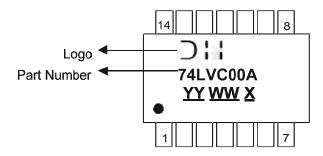
Notes: 7. The taping orientation and tape details can be found at http://www.diodes.com/datasheets/ap02007.pdf

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Marking Information

(1) SO-14, TSSOP-14



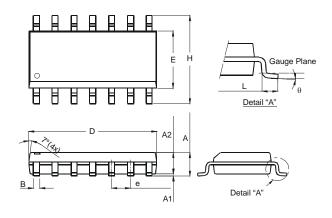
YY: Year: 08, 09,10~ WW: Week: 01~52; 52 represents 52 and 53 week

 \underline{X} : Internal Code

Part Number	Package
74LVC00AS14	SO-14
74LVC00AT14	TSSOP-14

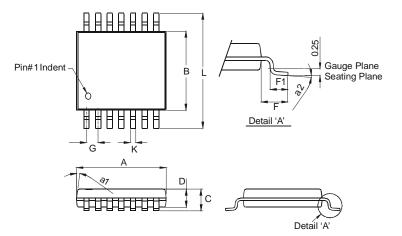
Package Outline Dimensions (All dimensions in mm.)

Package Type: SO-14



	SO-14				
Dim	Min	Max			
Α	1.47	1.73			
A1	0.10	0.25			
A2	1.45	Тур			
В	0.33	0.51			
D	8.53	8.74			
Е	3.80	3.99			
е	1.27	Тур			
Н	5.80	6.20			
L	0.38	1.27			
θ	0°	8°			
All Dimensions in mm					

Package Type: TSSOP-14

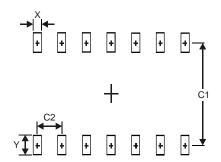


TSSOP-14		
Dim	Min	Max
a1	7° (4X)	
a2	0°	8°
Α	4.9	5.10
В	4.30	4.50
С	_	1.2
D	0.8	1.05
F	1.00 Typ	
F1	0.45	0.75
G	0.65 Typ	
K	0.19	0.30
Ĺ	6.40 Typ	
All Dimensions in mm		



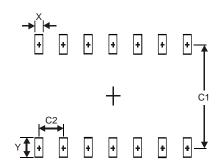
Suggested Pad Layout

Package Type: SO-14



Dimensions	Value (in mm)
Х	0.60
Y	1.50
C1	5.4
C2	1 27

Package Type: TSSOP-14



Dimensions	Value (in mm)
Х	0.45
Y	1.45
C1	5.9
C2	0.65



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